



PMV40UN2

30 V, N-channel Trench MOSFET

24 April 2014

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability of 1000 mW

3. Applications

- LED driver
- Power management
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_J = 25\text{ }^{\circ}\text{C}$		-	-	30	V
V_{GS}	gate-source voltage			-12	-	12	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; t \leq 5\text{ s}$	[1]	-	-	4.4	A
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 3.7\text{ A}; T_J = 25\text{ }^{\circ}\text{C}$		-	36	44	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

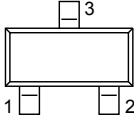
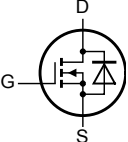


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-236AB (SOT23)	 017aaa253
2	S	source		
3	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV40UN2	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code
	[1]
PMV40UN2	%K8

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ }^{\circ}\text{C}$		-	30	V
V_{GS}	gate-source voltage			-12	12	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; t \leq 5\text{ s}$	[1]	-	4.4	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	3.7	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 100\text{ }^{\circ}\text{C}$	[1]	-	2.3	A
I_{DM}	peak drain current	$T_{amb} = 25\text{ }^{\circ}\text{C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$		-	16	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$	[2]	-	490	mW
			[1]	-	1000	mW
		$T_{sp} = 25\text{ }^{\circ}\text{C}$		-	5000	mW
T_j	junction temperature			-55	150	$^{\circ}\text{C}$
T_{amb}	ambient temperature			-55	150	$^{\circ}\text{C}$
T_{stg}	storage temperature			-65	150	$^{\circ}\text{C}$
Source-drain diode						
I_S	source current	$T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	0.9	A

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2 .
- [2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

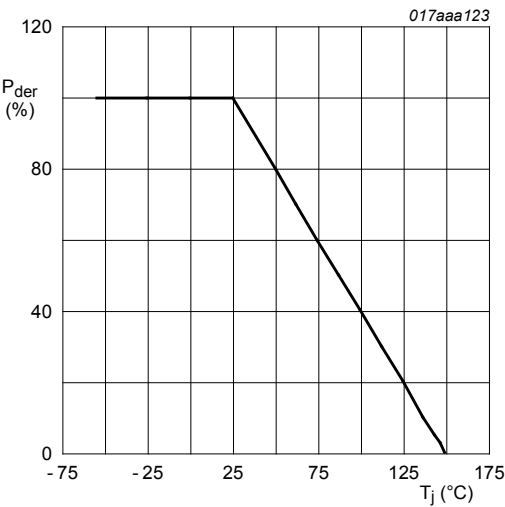


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

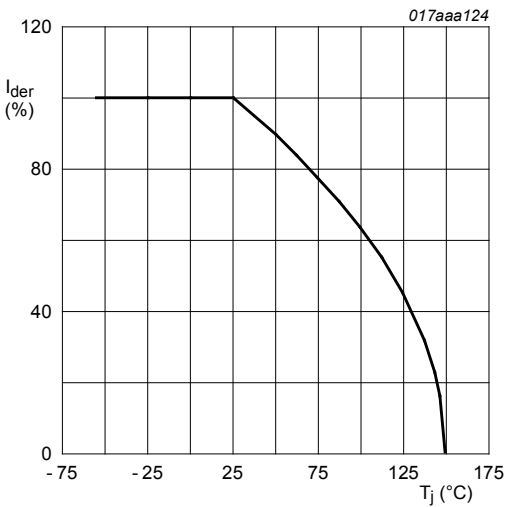


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

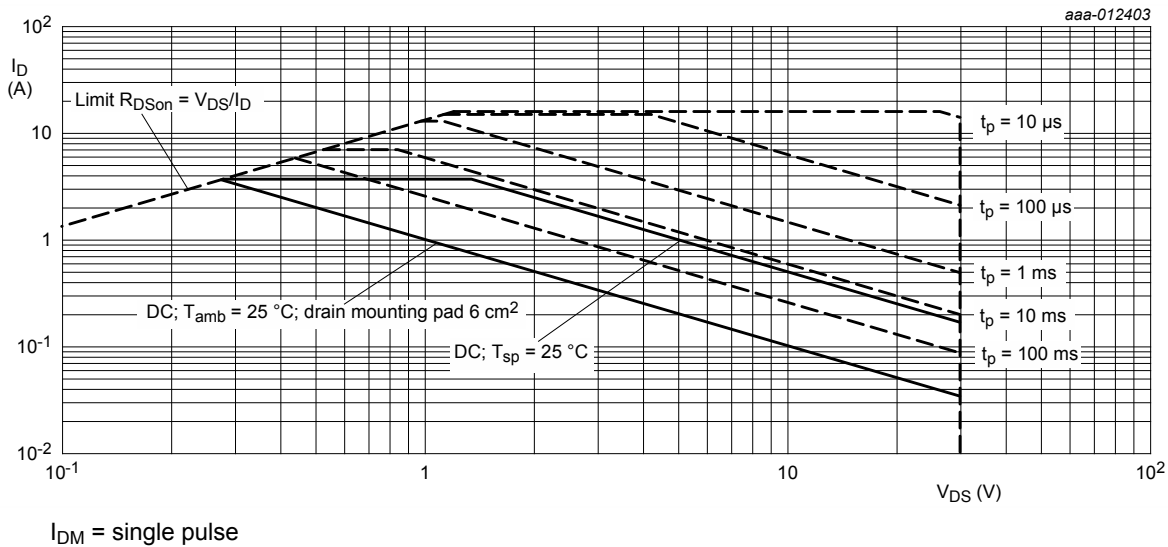


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	217	255	K/W
			[2]	-	105	124	K/W
		$t \leq 5$ s	[2]	-	73	86	K/W

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	20	25	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

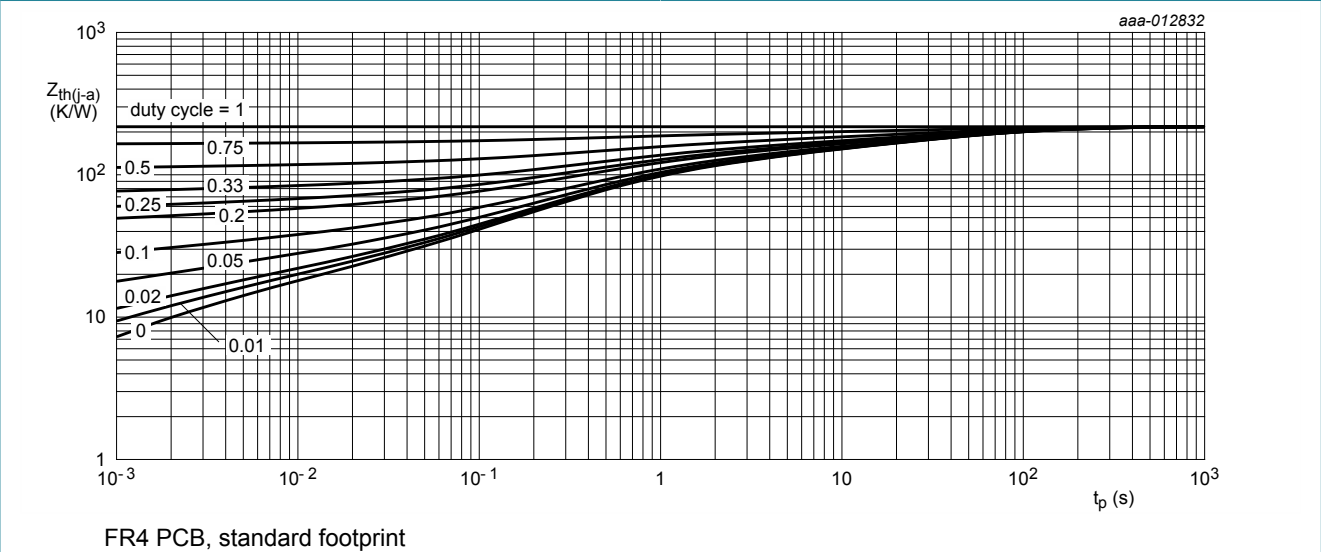


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

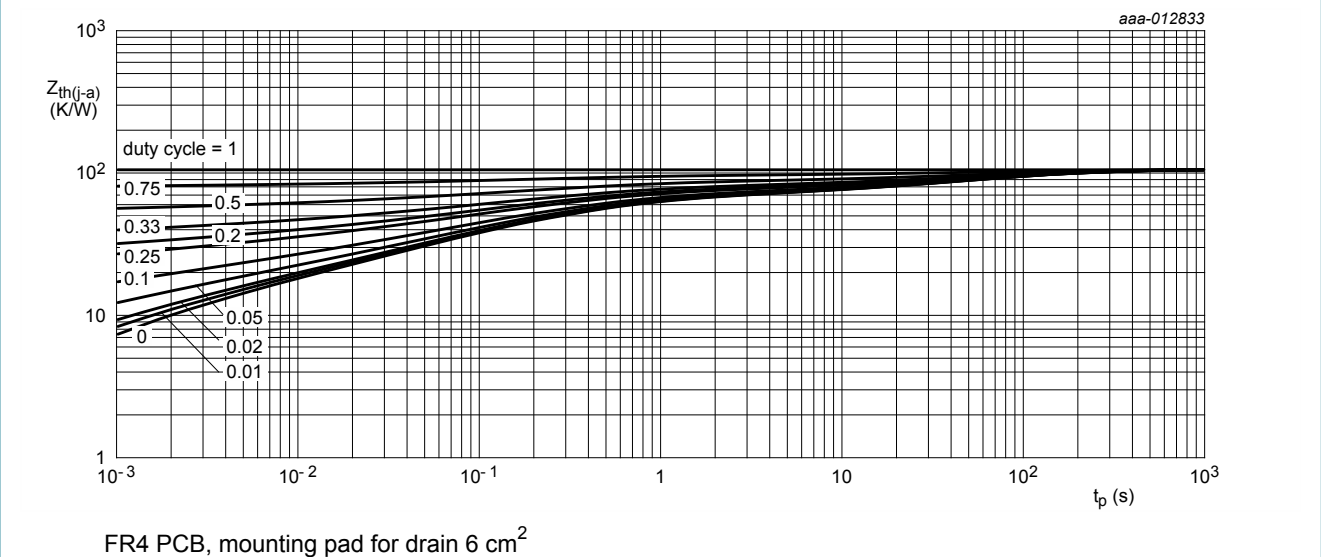


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		30	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C		0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C		-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C		-	-	100	nA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C		-	-	-100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 3.7 A; T _j = 25 °C		-	36	44	mΩ
		V _{GS} = 4.5 V; I _D = 3.7 A; T _j = 150 °C		-	62	75	mΩ
		V _{GS} = 2.5 V; I _D = 3.4 A; T _j = 25 °C		-	43	53	mΩ
		V _{GS} = 1.8 V; I _D = 0.5 A; T _j = 25 °C		-	56	78	mΩ
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 2 A; T _j = 25 °C		-	10.9	-	S
R _G	gate resistance	f = 1 MHz; T _j = 25 °C		-	8.7	-	Ω
Dynamic characteristics							
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 3.7 A; V _{GS} = 4.5 V; T _j = 25 °C		-	7	12	nC
Q _{GS}	gate-source charge			-	0.9	-	nC
Q _{GD}	gate-drain charge			-	1.7	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C		-	635	-	pF
C _{oss}	output capacitance			-	40	-	pF
C _{rss}	reverse transfer capacitance			-	35	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 3.7 A; V _{GS} = 4.5 V; R _{G(ext)} = 6 Ω; T _j = 25 °C		-	9	-	ns
t _r	rise time			-	23	-	ns
t _{d(off)}	turn-off delay time			-	34	-	ns
t _f	fall time			-	12	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 0.9 A; V _{GS} = 0 V; T _j = 25 °C		-	0.7	1.2	V

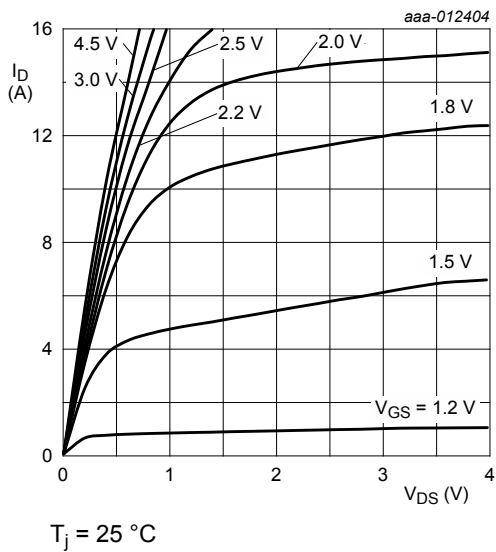


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

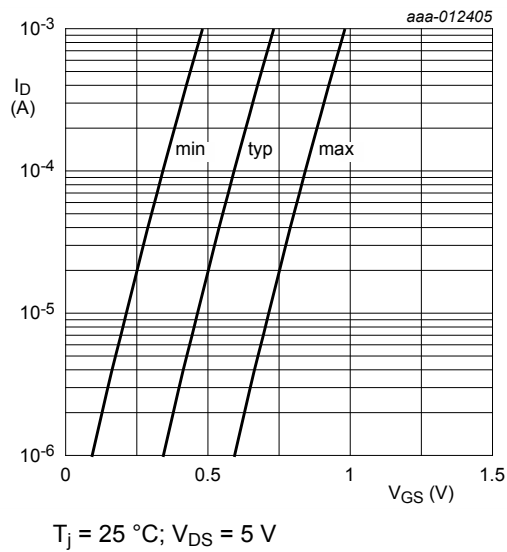


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

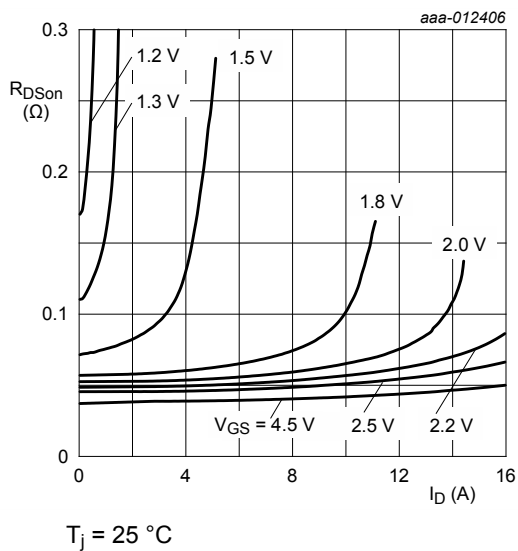


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

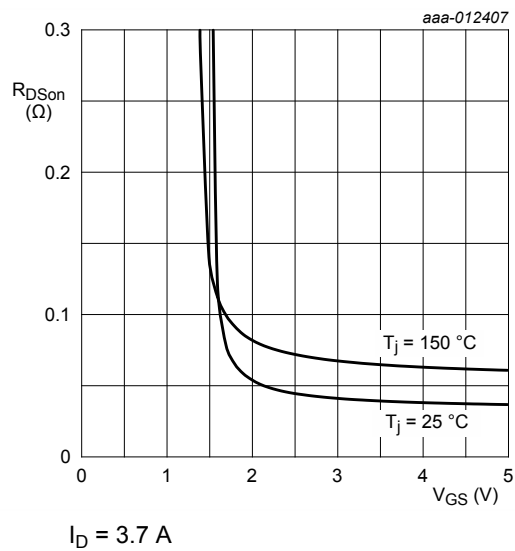


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

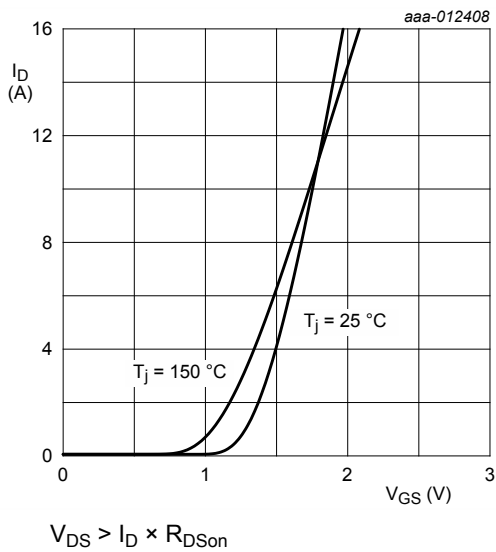


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

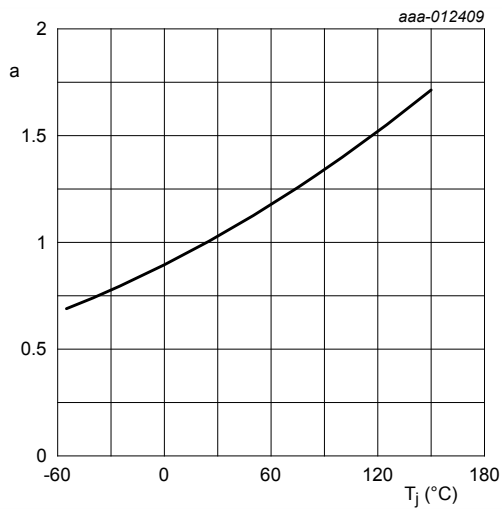


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DS(on)}}{R_{DS(on)25\text{ °C}}}$$

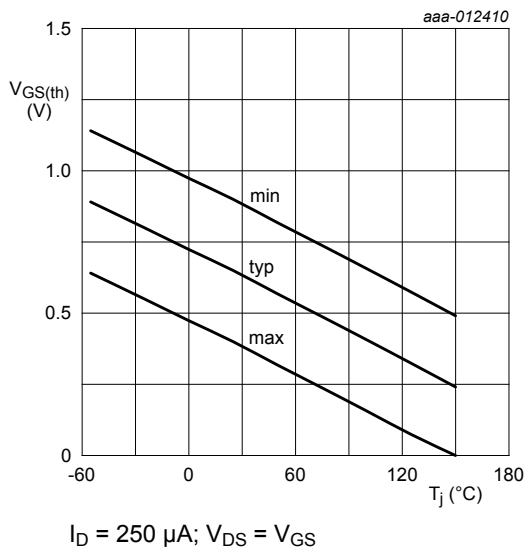


Fig. 12. Gate-source threshold voltage as a function of junction temperature

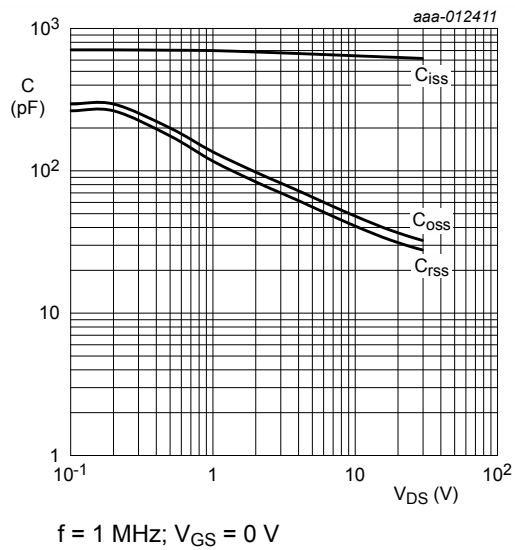


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

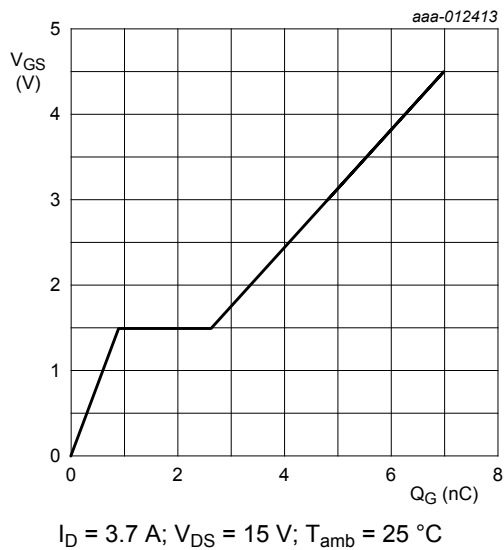


Fig. 14. Gate-source voltage as a function of gate charge; typical values

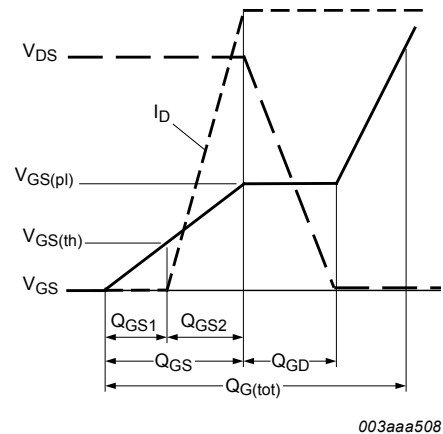


Fig. 15. MOSFET transistor: Gate charge waveform definitions

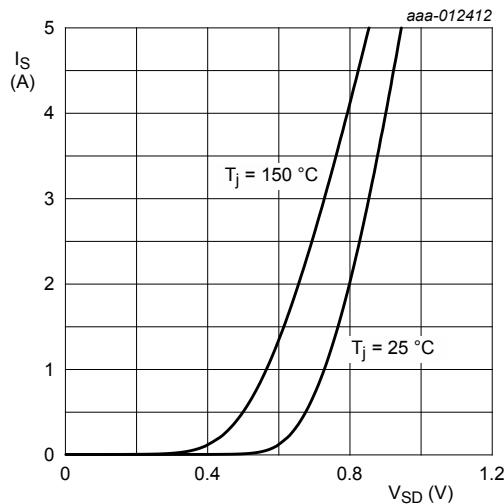


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

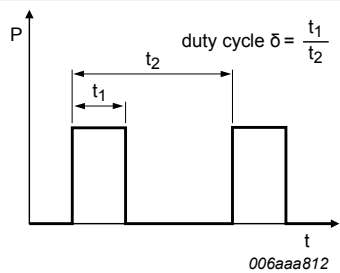


Fig. 17. Duty cycle definition

12. Package outline

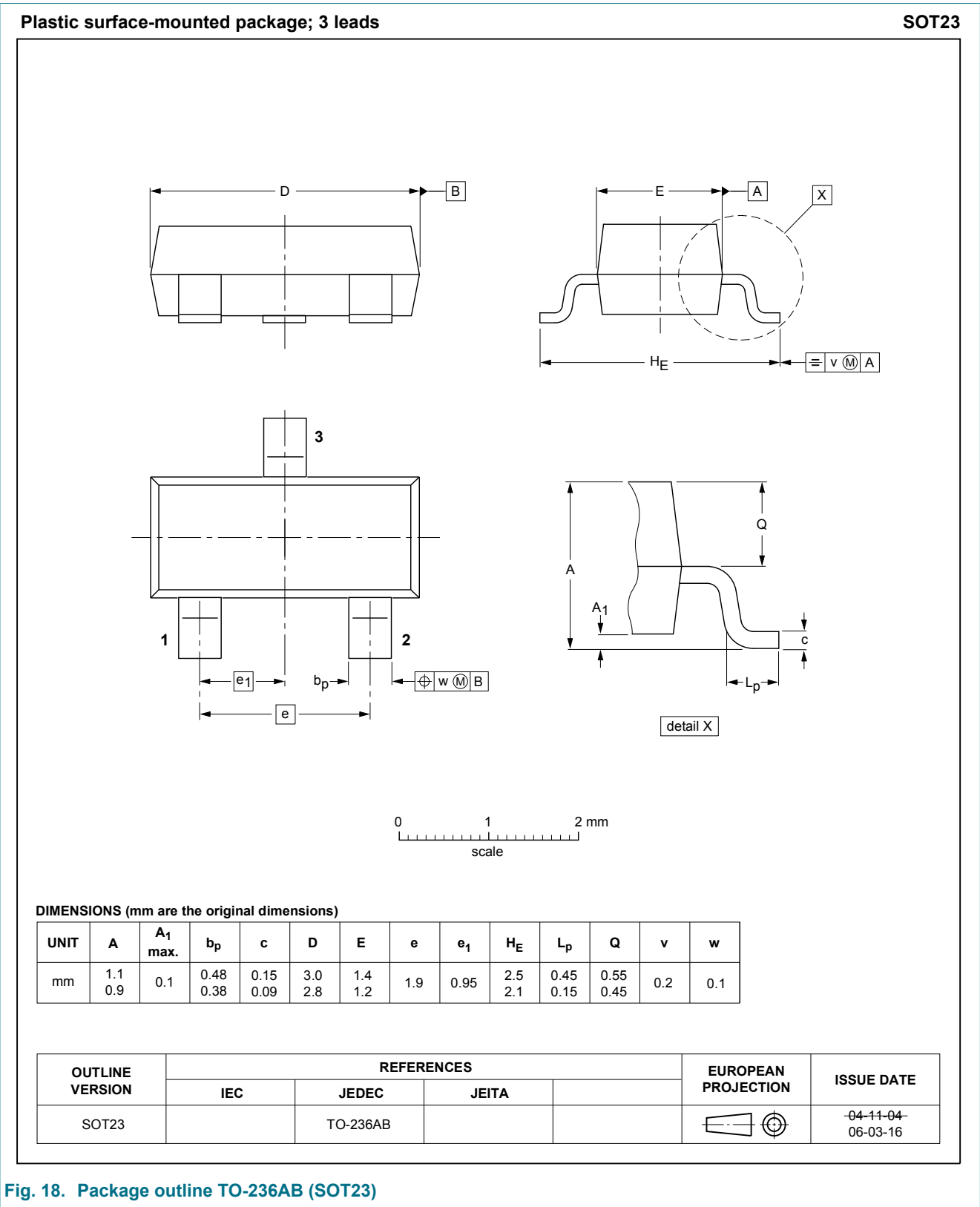


Fig. 18. Package outline TO-236AB (SOT23)

13. Soldering

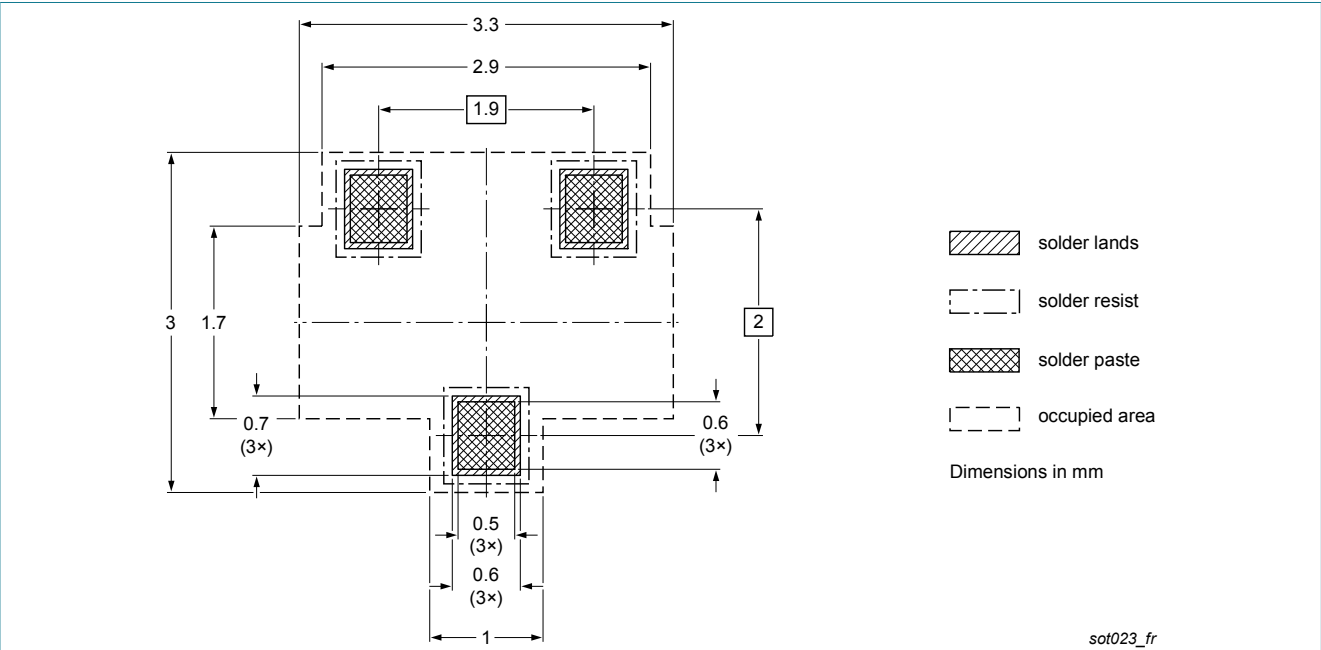


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

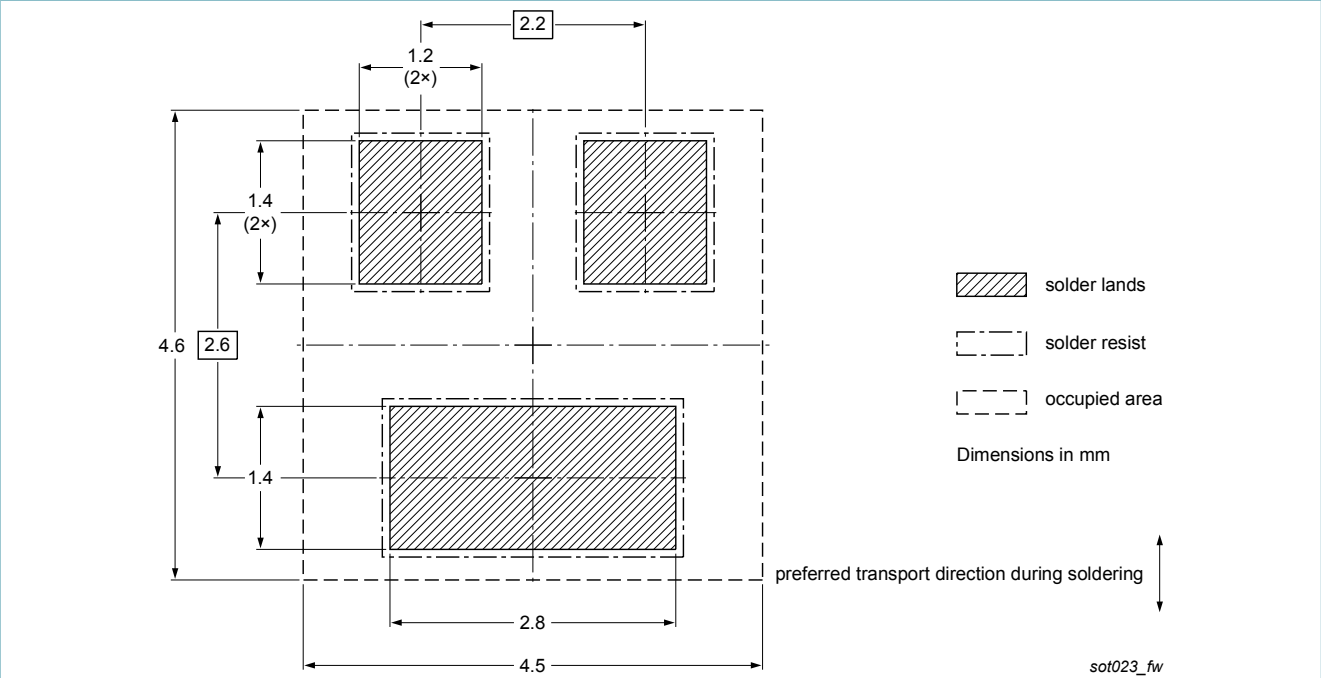


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV40UN2 v.1	20140424	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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